

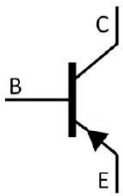
/ Descriptions

WR0<50 P SQS Silicon PNP transistor in a TO-92LM Plastic Package.

/ Features

NWF655 :
Complementary pair with KTC3227.

General purpose application.



PIN1 Base PIN 2 Collector PIN 3 Emitter

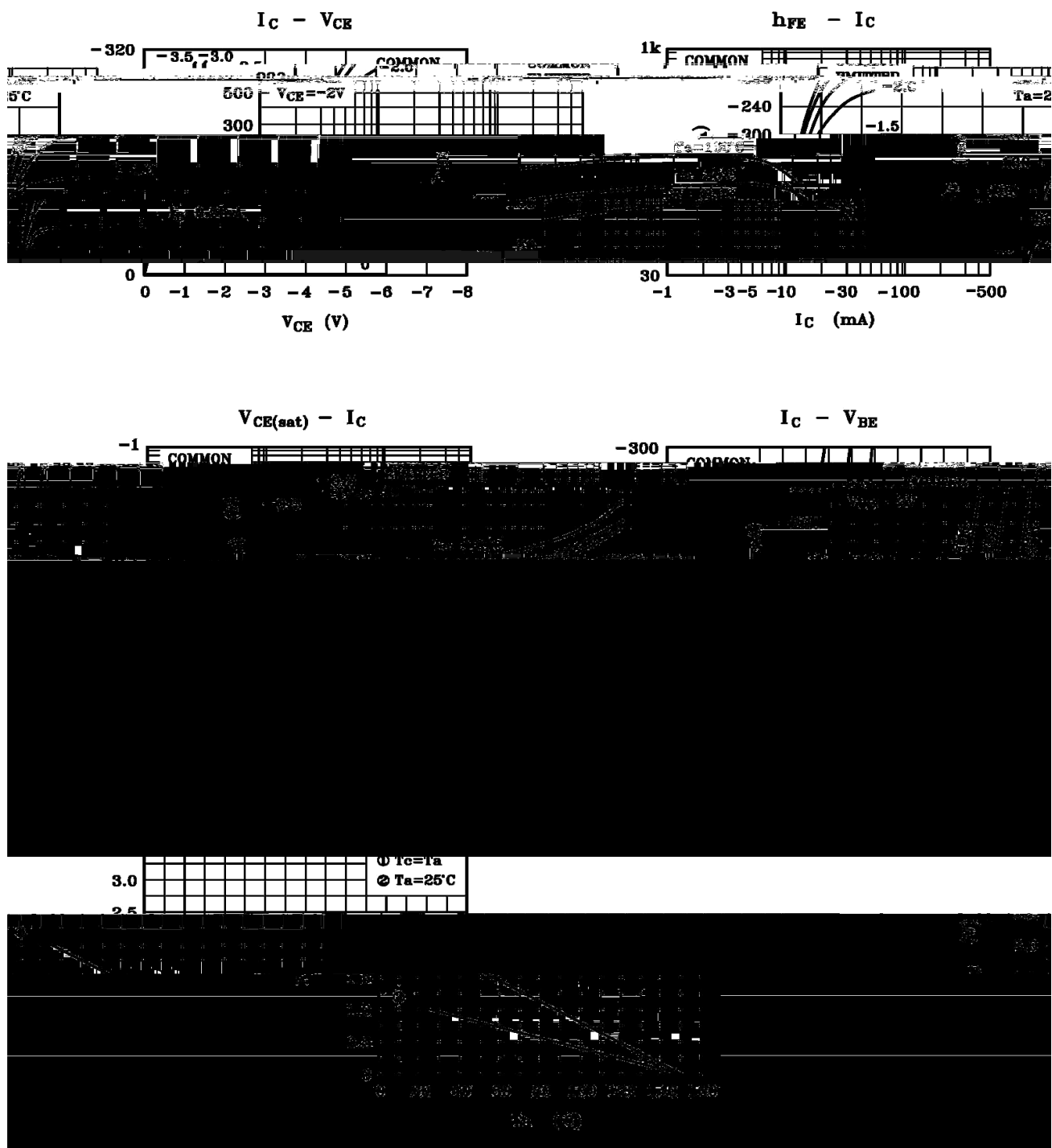
/ h_{FE} Classifications & Marking

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-400	mA
Emitter Current - Continuous	I_E	400	mA
Collector Power Dissipation	P_C	1.0	W
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -5.0mA$ $I_B = 0$	-80			V

CollectorCut-Of I V

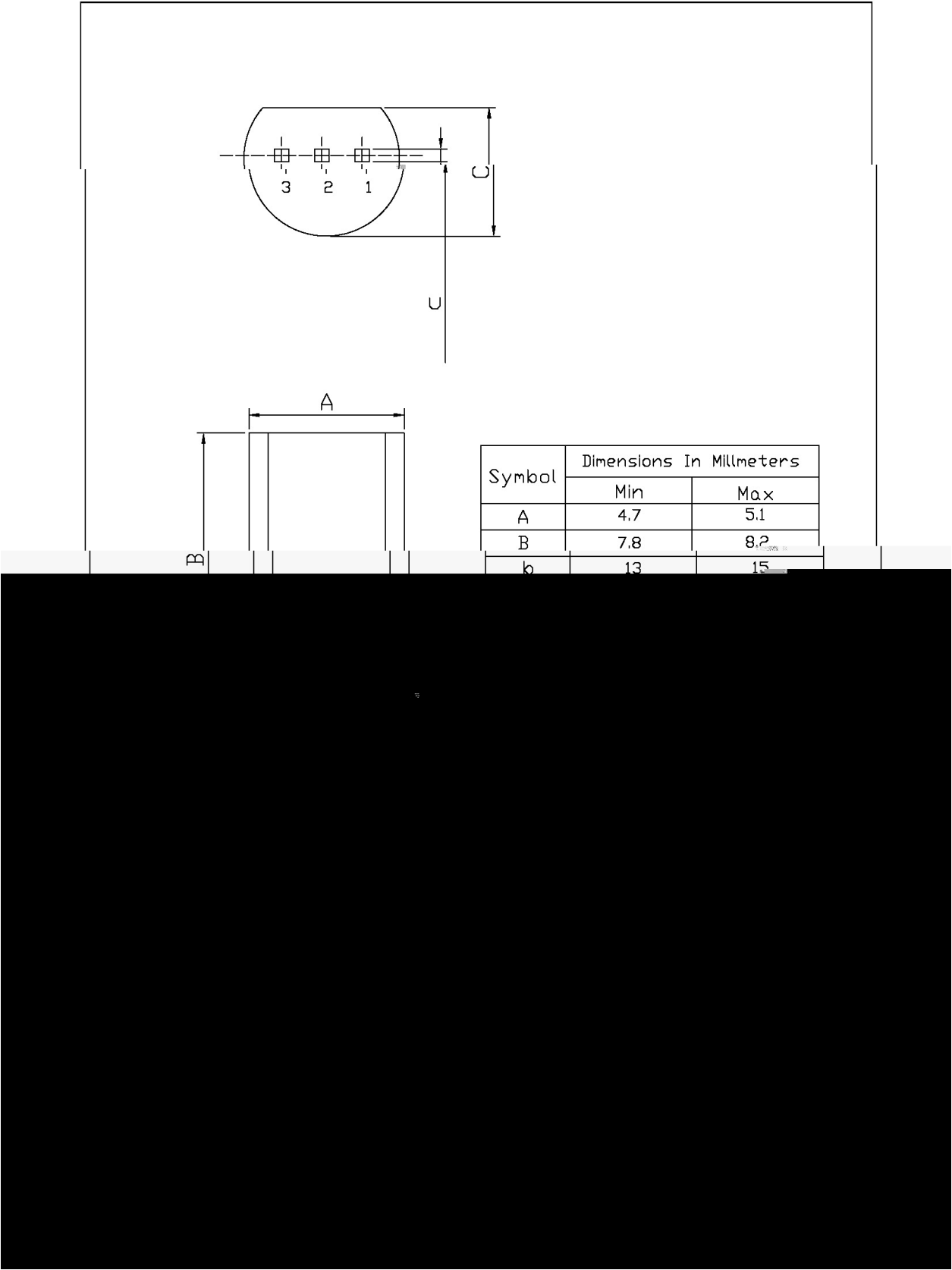
/ Electrical Characteristic Curve



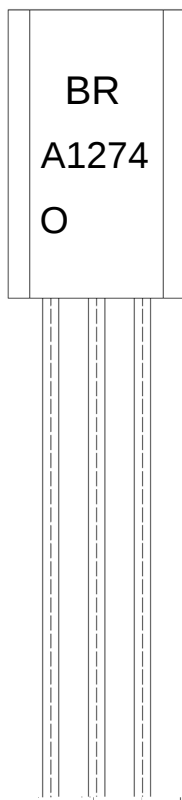
/ Package Dimensions

T0-92LM

Unit: mm



/ Marking Instructions



EU:

D45 : 7

R: k_{IH}

Note:

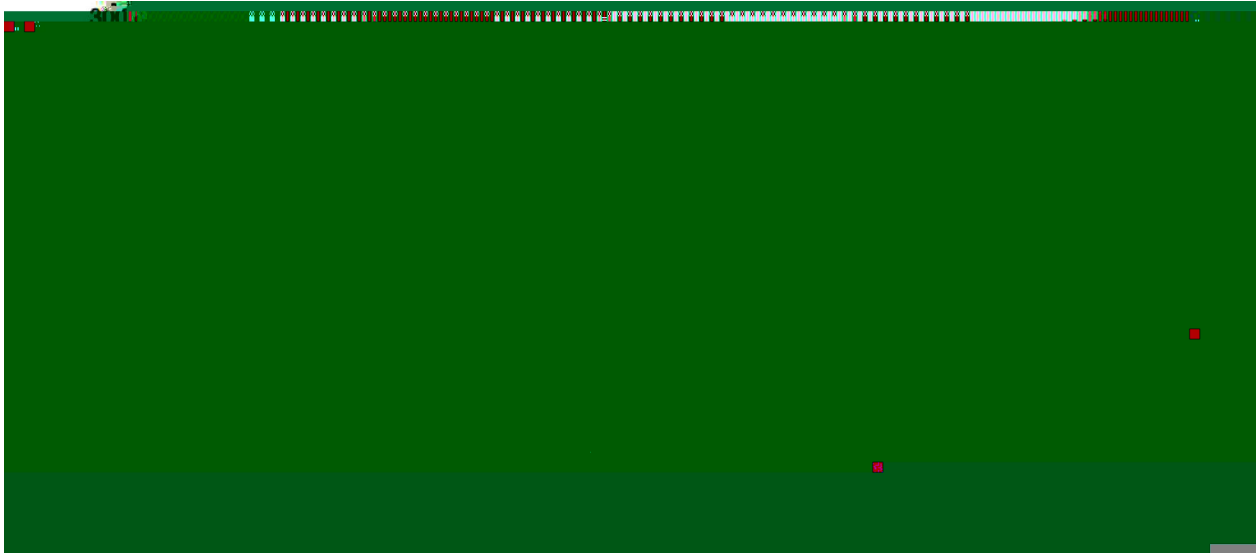
BR: Company Code.

A1274: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|------|----|----------|---|
| 1 | 25 | 150% | 60 | 90sec; | 1.Preheating:25~150%, Time:60~90sec. |
| 2 | 255 | ±5% | 5 | ±0.5sec; | 2.Peak Temp.:255 ±5%, Duration:5 ±0.5sec. |
| 3 | | | 2 | 10%/sec. | 3. Cooling Speed: 2~10%/sec. |

/ Resistance to Soldering Heat Test Conditions

270 ±5% 10 ±1 sec. Temp.:270 ±5% Time:10 ±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)

/ AMMO

Package Type	Units					Dimension		(unit mm3)

/ Notices